

Adam T Neal

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

36
papers

7,068
citations

22
h-index

37
g-index

37
ext. papers

7,996
ext. citations

5.1
avg, IF

5.96
L-index

#	Paper	IF	Citations
36	Gallium oxide power electronics. <i>APL Materials</i> , 2022 , 10, 029201	5.7	33
35	Si doping in MOCVD grown (010) $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ thin films. <i>Journal of Applied Physics</i> , 2022 , 131, 145301	2.5	5
34	Pulsed Power Performance of Ga_2O_3 MOSFETs at L-Band. <i>IEEE Electron Device Letters</i> , 2020 , 41, 989-992	4.4	19
33	Reduction of unintentional Si doping in Ga_2O_3 grown via plasma-assisted molecular beam epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020 , 38, 043403	2.9	15
32	Electrical Properties 1. <i>Springer Series in Materials Science</i> , 2020 , 389-405	0.9	
31	MOCVD growth of high purity Ga_2O_3 epitaxial films using trimethylgallium precursor. <i>Applied Physics Letters</i> , 2020 , 117, 262101	3.4	34
30	Lateral Ga_2O_3 field effect transistors. <i>Semiconductor Science and Technology</i> , 2020 , 35, 013002	1.8	38
29	Study of defects in Ga_2O_3 by isothermal capacitance transient spectroscopy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2019 , 37, 041204	1.3	3
28	Zeeman spin-splitting in the (010) Ga_2O_3 two-dimensional electron gas. <i>Applied Physics Letters</i> , 2019 , 115, 262103	3.4	0
27	Demonstration of high mobility and quantum transport in modulation-doped $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3/\text{Ga}_2\text{O}_3$ heterostructures. <i>Applied Physics Letters</i> , 2018 , 112, 173502	3.4	192
26	Donors and deep acceptors in Ga_2O_3 . <i>Applied Physics Letters</i> , 2018 , 113, 062101	3.4	148
25	Towards High-Mobility Heteroepitaxial Ga_2O_3 on Sapphire Dependence on The Substrate Off-Axis Angle. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700467	1.6	51
24	Ga_2O_3 defect study by steady-state capacitance spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 091101	1.4	12
23	P-type conduction in two-dimensional MoS_2 via oxygen incorporation. <i>Applied Physics Letters</i> , 2017 , 110, 193103	3.4	46
22	Ge-Doped $\beta\text{-Ga}_2\text{O}_3$ MOSFETs. <i>IEEE Electron Device Letters</i> , 2017 , 38, 775-778	4.4	124
21	Incomplete Ionization of a 110 meV Unintentional Donor in Ga_2O_3 and its Effect on Power Devices. <i>Scientific Reports</i> , 2017 , 7, 13218	4.9	60
20	Weak localization in few-layer black phosphorus. <i>2D Materials</i> , 2016 , 3, 024003	5.9	15

19	Heteroepitaxy of N-type Ga_2O_3 thin films on sapphire substrate by low pressure chemical vapor deposition. <i>Applied Physics Letters</i> , 2016 , 109, 132103	3.4	96
18	Transport studies in 2D transition metal dichalcogenides and black phosphorus. <i>Journal of Physics Condensed Matter</i> , 2016 , 28, 263002	1.8	10
17	The Effect of Dielectric Capping on Few-Layer Phosphorene Transistors: Tuning the Schottky Barrier Heights. <i>IEEE Electron Device Letters</i> , 2014 , 35, 795-797	4.4	142
16	Ambipolar phosphorene field-effect transistors with dielectric capping 2014 ,		4
15	Switching mechanism in single-layer molybdenum disulfide transistors: an insight into current flow across Schottky barriers. <i>ACS Nano</i> , 2014 , 8, 1031-8	16.7	202
14	Two-dimensional TaSe ₂ metallic crystals: spin-orbit scattering length and breakdown current density. <i>ACS Nano</i> , 2014 , 8, 9137-42	16.7	40
13	Phosphorene: an unexplored 2D semiconductor with a high hole mobility. <i>ACS Nano</i> , 2014 , 8, 4033-41	16.7	4487
12	Magneto-transport in MoS ₂ : phase coherence, spin-orbit scattering, and the hall factor. <i>ACS Nano</i> , 2013 , 7, 7077-82	16.7	78
11	Molecular Doping of Multilayer MoS_2 Field-Effect Transistors: Reduction in Sheet and Contact Resistances. <i>IEEE Electron Device Letters</i> , 2013 , 34, 1328-1330	4.4	196
10	Statistical study of deep submicron dual-gated field-effect transistors on monolayer chemical vapor deposition molybdenum disulfide films. <i>Nano Letters</i> , 2013 , 13, 2640-6	11.5	168
9	(Invited) Fundamentals in MoS ₂ Transistors: Dielectric, Scaling and Metal Contacts. <i>ECS Transactions</i> , 2013 , 58, 203-208	1	17
8	Metal contacts to MoS ₂ : A two-dimensional semiconductor 2012 ,		33
7	Size-Dependent-Transport Study of $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ Gate-All-Around Nanowire MOSFETs: Impact of Quantum Confinement and Volume Inversion. <i>IEEE Electron Device Letters</i> , 2012 , 33, 967-969	4.4	44
6	Channel length scaling of MoS ₂ MOSFETs. <i>ACS Nano</i> , 2012 , 6, 8563-9	16.7	594
5	Effects of (NH ₄) ₂ S passivation on the off-state performance of 3-dimensional InGaAs metal-oxide-semiconductor field-effect transistors. <i>Applied Physics Letters</i> , 2011 , 99, 152113	3.4	63
4	(Invited) ALD High-k as a Common Gate Stack Solution for Nanoelectronics. <i>ECS Transactions</i> , 2010 , 28, 51-68	1	3
3	(Invited) Atomic-Layer-Deposited High-k Dielectric Integration on Epitaxial Graphene. <i>ECS Transactions</i> , 2010 , 33, 459-466	1	4
2	Intrinsic doping and gate hysteresis in graphene field effect devices fabricated on SiO ₂ substrates. <i>Journal of Physics Condensed Matter</i> , 2010 , 22, 334214	1.8	91

1 Electronic Transport Properties in Top-Gated Epitaxial Graphene on Silicon Carbide with ALD Al₂O₃ High-K Dielectric **2010**,

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